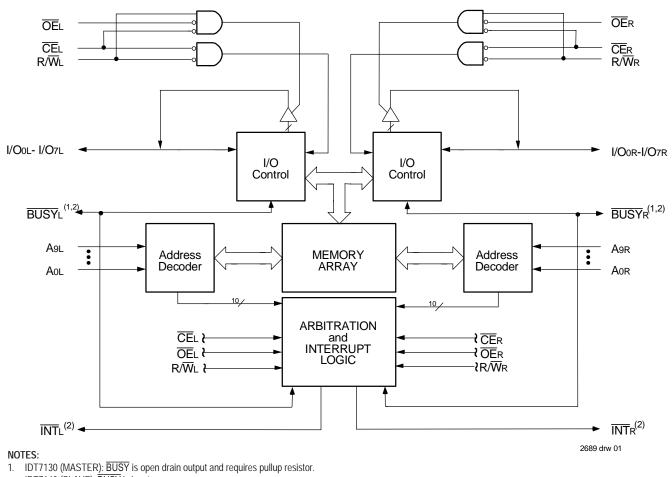
| 1 | IIGH SPEED K X 8 DUAL-PORT TATIC SRAM | IDT7130SA/LA IDT7140SA/LA |
|---|--|--|
| LEAD FINISH (SnPb) ARE IN EOL P | ROCESS - LAST TIME BUY EXPIRES | S JUNE 15, 2018 |
| Features High-speed access Commercial: 20/25/35/55/100ns (max.) Industrial: 25/55/100ns (max.) Military: 25/35/55/100ns (max.) Low-power operation IDT7130/IDT7140SA Active: 550mW (typ.) Standby: 5mW (typ.) IDT7130/IDT7140LA Active: 550mW (typ.) MASTER IDT7130 easily expands data bus width to 16-or more-bits using SLAVE IDT7140 | On-chip port arbitration logic (IE BUSY output flag on IDT7130; BI INT flag for port-to-port commun Fully asynchronous operation-2V da TTL-compatible, single 5V ±10% Military product compliant to MII Industrial temperature range (-4 for selected speeds Available in 48-pin DIP, LCC and PLCC, and 64-pin STOFP and TC r- | USY input on IDT7140 nication om either port ta retention (LA only) power supply L-PRF-38535 QML 0°C to +85°C) is available I Ceramic Flatpack, 52-pin QFP |

Functional Block Diagram



1

IDT7140 (SLAVE): BUSY is input.

2. Open drain output: requires pullup resistor.

FEBRUARY 2018

Military, Industrial and Commercial Temperature Ranges

Description

The IDT7130/IDT7140 are high-speed 1K x 8 Dual-Port Static RAMs. The IDT7130 is designed to be used as a stand-alone 8-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7140 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 16-or-more-bit memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

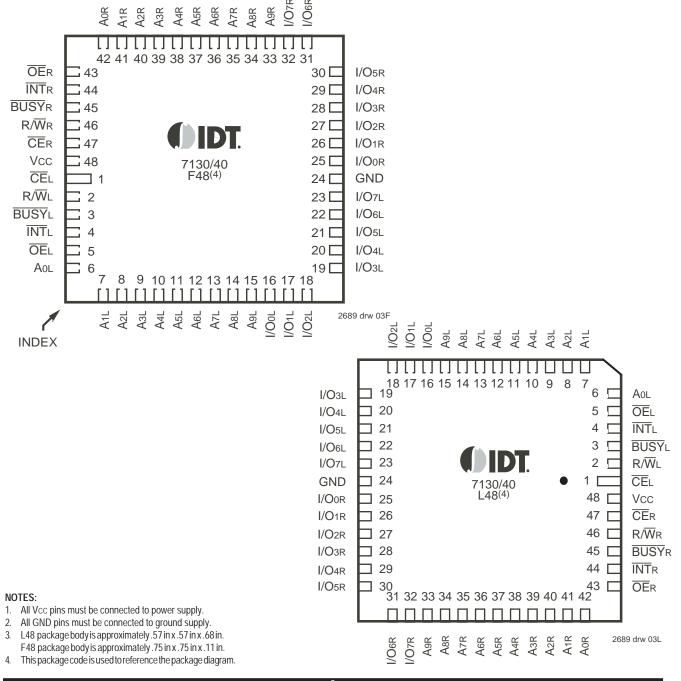
Both devices provide two independent ports with separate control, address, and I/O pins that permit independent asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by \overline{CE} , permits the on chip circuitry

Pin Configurations^(1,2,3)

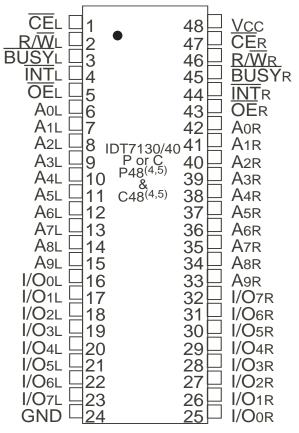
of each port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 550mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT7130/IDT7140 devices are packaged in 48-pin sidebraze or plastic DIPs, LCCs, flatpacks, 52-pin PLCC, and 64-pin TQFP and STQFP. Military grade products are manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.



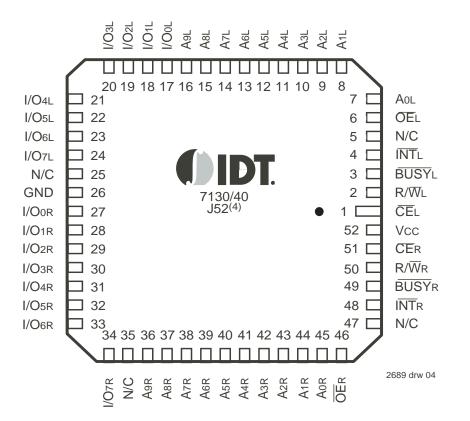
Pin Configurations^(1,2,3) (con't.)



2689 drw 02

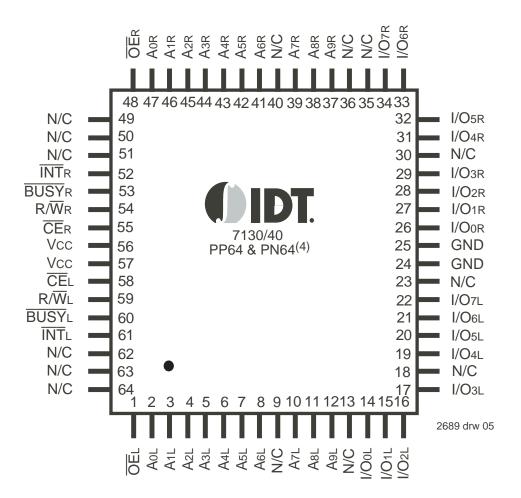
- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. P48 package body is approximately .55 in x .61 in x .19 in.
- C48 package body is approximately .62 in x 2.43 in x .15 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Configurations^(1,2,3) (con't.)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. J52-1 package body is approximately .75 in x .75 in x .17 in.
- 4. This package code is used to reference the package diagram.

PinConfigurations^(1,2,3) (con't.)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. PP64 package body is approximately 10 mm x 10 mm x 1.4mm. PN64 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram

Military, Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings⁽¹⁾

| Symbol | Rating | Commercial & Industrial | Military | Unit |
|----------------------|--|----------------------------|--------------|------|
| Vterm ⁽²⁾ | Terminal Voltage with Respect to GND | -0.5 to +7.0 | -0.5 to +7.0 | V |
| Tbias | Temperature Under Bias | -55 to +125 | -65 to +135 | °C |
| Tstg | Storage Temperature | -65 to +150 | -65 to +150 | ٥C |
| ЮИТ | DC Output Current | 50 | 50 | mA |

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute
- maximum rating conditions for extended periods may affect reliability.
 VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to < 20mA for the period of VTERM > Vcc + 10%.

Capacitance (TA = +25°C, f = 1.0MHz) STQFP and TQFP Packages Only

| Symbol | Parameter ⁽¹⁾ | Conditions | Max. | Unit |
|--------|--------------------------|------------|------|-------------|
| Cin | Input Capacitance | VIN = 3dV | 9 | pF |
| Соит | Output Capacitance | Vout = 3dV | 10 | pF |
| | | | | 2689 tbl 05 |

NOTES:

1. This parameter is determined by device characterization but is not production tested.

3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended DC Operating Conditions

| Symbol | Parameter | Min. | Тур. | Мах. | Unit |
|--------|--------------------|---------------------|------|--------------------|------|
| Vcc | Supply Voltage | 4.5 | 5.0 | 5.5 | V |
| GND | Ground | 0 | 0 | 0 | V |
| Vih | Input High Voltage | 2.2 | | 6.0 ⁽²⁾ | V |
| VIL | Input Low Voltage | -0.5 ⁽¹⁾ | _ | 0.8 | V |

NOTES:

2689 tbl 01

1. VIL (min.) \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

| Grade | Ambient Temperature | GND | Vcc |
|------------|------------------------|-----|-------------------|
| Military | -55°C to +125°C | 0V | 5.0V <u>+</u> 10% |
| Commercial | 0°C to +70°C | 0V | 5.0V <u>+</u> 10% |
| Industrial | -40°C to +85°C | 0V | 5.0V <u>+</u> 10% |
| | | | 2689 tbl 03 |

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

| | | | - | 0SA 0SA | - | 0LA 0LA | |
|--------|--|---|------|------------|------|------------|------|
| Symbol | Parameter | Test Conditions | Min. | Max. | Min. | Max. | Unit |
| lu | Input Leakage Current ⁽¹⁾ | Vcc = 5.5V, VIN = 0V to Vcc | _ | 10 | - | 5 | μA |
| ILO | Output Leakage Current ⁽¹⁾ | $\frac{V_{CC}}{CE}$ = V _H , Vout = 0V to Vcc | — | 10 | _ | 5 | μA |
| Vol | Output Low Voltage (I/Oo-I/O7) | IOL = 4mA | _ | 0.4 | _ | 0.4 | V |
| Vol | Open Drain O <u>utput</u> Low Voltage (BUSY, INT) | lo∟ = 16mA | _ | 0.5 | | 0.5 | V |
| Vон | Output High Voltage | Юн = -4mA | 2.4 | - | 2.4 | _ | V |

NOTE:

1. At Vcc ≤ 2.0V leakages are undefined.

2689 tbl 04

2689 tbl 02

Military, Industrial and Commercial Temperature Ranges

2689 tbl 06a

2689 tbl 06b

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(1,5)}$ (Vcc = 5.0V ± 10%)

| | | | | | 7140 | X20 ⁽²⁾ X20 ⁽²⁾ I Only | 7140 Com | 0X25 0X25 'I, Ind litary | 7140 Co |)X35)X35 m'l litary | |
|--------|---|--|--------------|----------|------------|--|-------------|-----------------------------------|------------|-------------------------------|------|
| Symbol | Parameter | Test Condition | Versie | on | Тур. | Мах. | Тур. | Мах. | Тур. | Мах. | Unit |
| lcc | Dynamic Operating Current (Both Ports Active) | CEL and CER = VIL, Outputs Disabled f = fMAX ⁽³⁾ | COM'L | SA LA | 110 110 | 250 200 | 110 110 | 220 170 | 110 110 | 165 120 | mA |
| | | T = IIWAX** | MIL & IND | SA LA | | | 110 110 | 280 220 | 110 110 | 230 170 | |
| ISB1 | Standby Current (Both Ports - TTL | \overline{CE}_{L} and $\overline{CE}_{R} = V_{IH}$ f = fMAX ⁽³⁾ | COM'L | SA LA | 30 30 | 65 45 | 30 30 | 65 45 | 25 25 | 65 45 | mA |
| | Level Inputs) | | MIL & IND | SA LA | | | 30 30 | 80 60 | 25 25 | 80 60 | |
| ISB2 | Standby Current (One Port - TTL Level Inputs) | $\overline{CE}^{*}_{A^{*}} = V_{IL}$ and $\overline{CE}^{*}_{B^{*}} = V_{H}^{(6)}$ Active Port OutputsDisabled, | COM'L | SA LA | 65 65 | 165 125 | 65 65 | 150 115 | 50 50 | 125 90 | mA |
| | Level inpuis) | f=fmax ⁽³⁾ | MIL & IND | SA LA | | | 65 65 | 160 125 | 50 50 | 150 115 | |
| ISB3 | Full Standby Current (Both Ports - CMOS Level Inputs) | \overline{CE}_{L} and $\overline{CER} \ge Vcc - 0.2V$, | COM'L | SA LA | 1.0 0.2 | 15 5 | 1.0 0.2 | 15 5 | 1.0 0.2 | 30 10 | mA |
| | Civios Lever Inpus) | $ \begin{array}{l} V_{IN} \geq Vcc - 0.2V \text{ or} \\ V_{IN} \leq 0.2V \text{, } f = 0^{(4)} \end{array} $ | MIL & IND | SA LA | | | 1.0 0.2 | 30 10 | | | |
| ISB4 | Full Standby Current (One Port - | $\frac{\overline{CE}^{*}A^{*}}{\overline{CE}^{*}B^{*}} \stackrel{\leq}{\geq} VCC - 0.2V^{(6)}$ | COM'L | SA LA | 60 60 | 155 115 | 60 60 | 145 105 | 45 45 | 110 85 | mA |
| | CMOS Level Inputs) | $V_{IN} \ge \overline{V}_{CC} - 0.2V$ or $V_{IN} \le 0.2V$ Active Port Outputs Disabled, $f = f_{MAX}^{(6)}$ | MIL & IND | SA LA | | | 60 60 | 155 115 | 45 45 | 145 105 | |

| | | | | | 714 Com | 0X55 0X55 'I, Ind litary | 7140 Com | X100 X100 I, Ind litary | |
|--------|---|---|--------------|----------|------------|-----------------------------------|-------------|----------------------------------|------|
| Symbol | Parameter | Test Condition | Versi | on | Тур. | Max. | Тур. | Max. | Unit |
| lcc | Dynamic Operating Current (Both Ports Active) | \overline{CE}_{L} and $\overline{CE}_{R} = V_{IL}$, Outputs Disabled f = fmax ⁽³⁾ | COM'L | SA LA | 110 110 | 155 110 | 110 110 | 155 110 | mA |
| | (DUIT POILS ACTIVE) | I = IMAX*' | MIL & IND | SA LA | 110 110 | 190 140 | 110 110 | 190 140 | |
| ISB1 | Standby Current (Both Ports - TTL Level Inputs) | \overline{CE}_{L} and $\overline{CE}_{R} = V_{IH}$ f = fMAX ⁽³⁾ | COM'L | SA LA | 20 20 | 65 35 | 20 20 | 55 35 | mA |
| | Level liipuis) | | MIL & IND | SA LA | 20 20 | 65 45 | 20 20 | 65 45 | |
| ISB2 | Standby Current (One Port - TTL Level Inputs) | \overline{CE} 'A" = VIL and \overline{CE} 'B" = VH ⁽⁶⁾ Active Port Outputs Disabled, f=fmax ⁽³⁾ | COM'L | SA LA | 40 40 | 110 75 | 40 40 | 110 75 | mA |
| | Level liipuis) | I=IMAX** | MIL & IND | SA LA | 40 40 | 125 90 | 40 40 | 125 90 | |
| ISB3 | Full Standby Current (Both Ports - CMOS Level Inputs) | $\overline{CE}L \text{ and } \\ \overline{CE}R \ge Vcc - 0.2V, \\ W_{WL} = Vcc - 0.2V, \\ \overline{CE}R \ge 0.2V, \\ \overline{CE}R \ge$ | COM'L | SA LA | 1.0 0.2 | 15 4 | 1.0 0.2 | 15 4 | mA |
| | Civios Lever Inpuis) | $ \begin{array}{l} V_{IN} \geq V_{CC} - 0.2V \text{ or} \\ V_{IN} \leq 0.2V, \ f = 0^{(4)} \end{array} $ | MIL & IND | SA LA | 1.0 0.2 | 30 10 | 1.0 0.2 | 30 10 | |
| ISB4 | Full Standby Current (One Port - CMOS Level Inputs) | $\overline{\underline{CE}}^* A^* \leq 0.2V \text{ and} \\ \overline{\overline{CE}}^* B^* \geq VCC - 0.2V^{(6)}$ | COM'L | SA LA | 40 40 | 100 70 | 40 40 | 95 70 | mA |
| | Civios Level Inpuls) | $V_{IN} \ge \overline{V}_{CC} - 0.2V$ or $V_{IN} \le 0.2V$ Active Port Outputs Disabled, $f = f_{MAX}^{(B)}$ | MIL & IND | SA LA | 40 40 | 110 85 | 40 40 | 110 80 | |

NOTES:

1. 'X' in part numbers indicates power rating (SA or LA).

2. PLCC, TQFP and STQFP packages only.

3. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tcyc, and using "AC TEST CONDITIONS" of input levels of GND to 3V.

4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.

5. Vcc = 5V, TA=+25°C for Typ and is not production tested. Vcc DC = 100 mA (Typ)

6. Port "A" may be either left or right port. Port "B" is opposite from port "A".

Military, Industrial and Commercial Temperature Ranges

Data Retention Characteristics (LA Version Only)

| | | | | 7' | 7130LA/7140LA | | |
|---------------------|--------------------------------------|---|-------------|--------------------|---------------------|------|-------------|
| Symbol | Parameter | Test Condition | 1 | Min. | Тур. ⁽¹⁾ | Мах. | Unit |
| Vdr | Vcc for Data Retention | | | 2.0 | - | _ | V |
| ICCDR | Data Retention Current | | MIL. & IND. | _ | 100 | 4000 | μA |
| | | Vcc = 2.0V, $\overline{CE} \ge$ Vcc -0.2V | COM'L. | _ | 100 | 1500 | |
| tcdr ⁽³⁾ | Chip Deselect to Data Retention Time | Vin \geq Vcc -0.2V or Vin \leq 0.2V | | 0 | _ | _ | ns |
| tR ⁽³⁾ | Operation Recovery Time | | | trc ⁽²⁾ | _ | _ | ns |
| 10750 | | • | | | | 2 | 2689 tbl 07 |

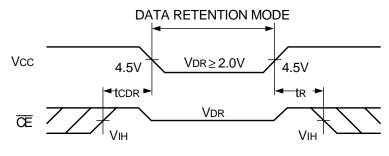
NOTES:

1. Vcc = 2V, TA = +25°C, and is not production tested.

2. tRC = Read Cycle Time

3. This parameter is guaranteed but not production tested.

Data Retention Waveform



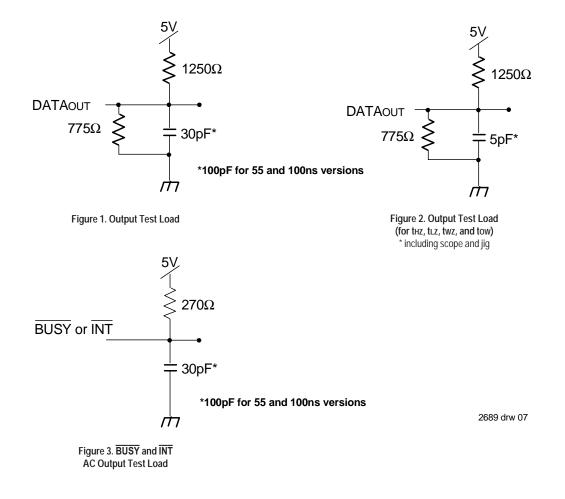
2692 drw 06

Military, Industrial and Commercial Temperature Ranges

AC Test Conditions

| Input Pulse Levels | GND to 3.0V |
|-------------------------------|-------------------|
| Input Rise/Fall Times | 5ns |
| Input Timing Reference Levels | 1.5V |
| Output Reference Levels | 1.5V |
| Output Load | Figures 1,2 and 3 |

2689 tbl 08



Military, Industrial and Commercial Temperature Ranges

2689 tbl 09b

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽³⁾

| | | 7140 | X20 ²⁾ X20 ²⁾ I Only | 7140 Com |)X25)X25 I, Ind litary | 714 Co | 0X35 0X35 m'l litary | |
|------------|--|------|--|-------------|----------------------------------|-----------|-------------------------------|------|
| Symbol | Parameter | Min. | Мах. | Min. | Мах. | Min. | Мах. | Unit |
| READ CYCLE | | | | - | | | | |
| trc | Read Cycle Time | 20 | | 25 | - | 35 | | ns |
| taa | Address Access Time | | 20 | | 25 | | 35 | ns |
| tace | Chip Enable Access Time | | 20 | | 25 | | 35 | ns |
| taoe | Output Enable Access Time | | 11 | _ | 12 | | 20 | ns |
| tон | Output Hold from Address Change | 3 | | 3 | | 3 | | ns |
| tLZ | Output Low-Z Time ^(1,4) | 0 | | 0 | | 0 | - | ns |
| tHZ | Output High-Z Time ^(1,4) | | 10 | | 10 | | 15 | ns |
| tPU | Chip Enable to Power Up Time ⁽⁴⁾ | 0 | | 0 | | 0 | | ns |
| tpd | Chip Disable to Power Down Time ⁽⁴⁾ | | 20 | | 25 | | 35 | ns |

2689 tbl 09a 7130X55 7130X100 7140X55 7140X100 Com'l, Ind Com'l, Ind & Military & Military Min. Unit Symbol Max. Min. Мах. Parameter READ CYCLE Read Cycle Time trc 55 100 _____ ns Address Access Time 55 100 tΑA _____ _____ ns **t**ACE Chip Enable Access Time 55 100 ns ____ _____ Output Enable Access Time 25 40 **t**AOE ____ _____ ns tон Output Hold from Address Change 3 10 ____ ns ____ Output Low-Z Time^(1,4) 5 5 t∟z ns Output High-Z Time^(1,4) 25 tHZ 40 ns Chip Enable to Power Up Time⁽⁴⁾ 0 0 t₽U ns ____ _____ Chip Disable to Power Down Time⁽⁴⁾ 50 50 t₽D ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage Output Test Load (Figure 2).

2. PLCC, TQFP and STQFP packages only.

3. 'X' in part numbers indicates power rating (SA or LA).

4. This parameter is guaranteed by device characterization, but is not production tested.

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IDT7130SA/LA and IDT7140SA/LA High-Speed 1K x 8 Dual-Port Static SRAM Military, Industrial and Commercial Temperature Ranges Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾ ADDRESS Image: Commercial Temperature Ranges DATAout PREVIOUS DATA VALID BUSYout Image: Commercial Temperature Ranges

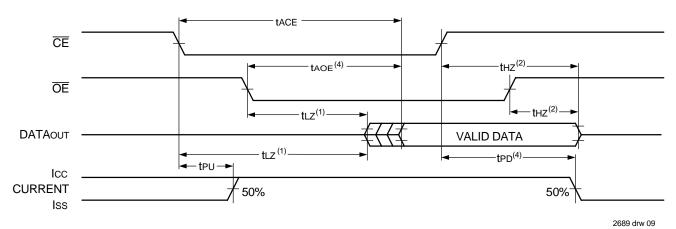
NOTES:

1. $R/\overline{W} = V_{IH}, \overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.

2. tedd delay is required only in the case where the opposite port is completing a write operation to the same the address location. For simultaneous read operations, BUSY has no relationship to valid output data.

3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

Timing Waveform of Read Cycle No. 2, Either Side⁽³⁾



- 1. Timing depends on which signal is asserted last, \overline{OE} or \overline{CE} .
- 2. Timing depends on which signal is deaserted first, \overline{OE} or \overline{CE} .
- 3. $R/\overline{W} = V_{H}$ and $\overline{OE} = V_{IL}$, and the address is valid prior to or coincidental with \overline{CE} transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

Military, Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽⁵⁾

| | | 7140 |)X20 ⁽²⁾)X20 ⁽²⁾ I Only | 7140 Com' |)X25)X25 I, Ind litary | 7140 Co | 0X35 0X35 vm'l litary | |
|--|---|------|--|--------------------------------------|------------------------------------|---------------------------------------|--------------------------------------|--|
| Symbol | Parameter | Min. | Мах. | Min. | Мах. | Min. | Мах. | Unit |
| WRITE CYCLI | E | | | | | | | |
| twc | Write Cycle $Time^{\scriptscriptstyle{(3)}}$ | 20 | | 25 | | 35 | | ns |
| tew | Chip Enable to End-of-Write | 15 | | 20 | | 30 | | ns |
| taw | Address Valid to End-of-Write | 15 | | 20 | | 30 | | ns |
| tas | Address Set-up Time | 0 | | 0 | | 0 | — | ns |
| twp | Write Pulse Width ⁽⁴⁾ | 15 | | 15 | | 25 | | ns |
| twr | Write Recovery Time | 0 | | 0 | | 0 | | ns |
| tow | Data Valid to End-of-Write | 10 | | 12 | | 15 | - | ns |
| tHZ | Output High-Z Time ⁽¹⁾ | | 10 | | 10 | | 15 | ns |
| tDH | Data Hold Time | 0 | | 0 | | 0 | — | ns |
| twz | Write Enable to Output in High-Z ⁽¹⁾ | | 10 | - | 10 | _ | 15 | ns |
| tow | Output Active from End-of-Write ⁽¹⁾ | 0 | _ | 0 | | 0 | | ns |
| | | | | - | | | | 2689 tbl 10 |
| | | | | 714 Com | 0X55 0X55 'I, Ind Ilitary | 7140 Com |)X100)X100 'I, Ind ilitary | |
| Symbol | Parameter | | | | | | 1 | |
| WRITE CYCL | | | | Min. | Max. | Min. | Max. | Unit |
| | E | | | Min. | Max. | Min. | Max. | Unit |
| twc | E Write Cycle Time ⁽³⁾ | | | Min . 55 | Мах. | Min . 100 | Max. | Unit ns |
| twc tew | | | | 1 | Max. | | Max. | 1 |
| | Write Cycle Time ⁽³⁾ | | | 55 | | 100 | Max. | ns |
| tEW | Write Cycle Time ⁽³⁾ Chip Enable to End-of-Write | | | 55 40 | | 100 90 | | ns ns |
| tew taw | Write Cycle Time ⁽³⁾ Chip Enable to End-of-Write Address Valid to End-of-Write | | | 55 40 40 | | 100 90 90 | | ns ns ns |
| tew taw tas | Write Cycle Time ⁽³⁾ Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time | | | 55 40 40 0 | | 100 90 90 0 | | ns ns ns ns |
| tew taw tas twp | Write Cycle Time ⁽³⁾ Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time Write Pulse Width ⁽⁴⁾ | | | 55 40 40 0 30 | | 100 90 90 0 55 | | ns ns ns ns |
| tew taw tas twp twr tow | Write Cycle Time ⁽³⁾ Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time Write Pulse Width ⁽⁴⁾ Write Recovery Time | | | 55 40 40 0 30 0 | | 100 90 90 0 55 0 | | ns ns ns ns ns ns |
| tew taw tas twp twr | Write Cycle Time ⁽³⁾ Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time Write Pulse Width ⁽⁴⁾ Write Recovery Time Data Valid to End-of-Write | | | 55 40 40 0 30 0 20 | | 100 90 90 0 55 0 40 | | ns ns ns ns ns ns ns ns |

NOTES:

tow

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.

0

0

2689 tbl 10b

2. PLCC, TQFP and STQFP packages only.

3. For MASTER/SLAVE combination, twc = tBAA + twp, since R/W = VIL must occur after tBAA.

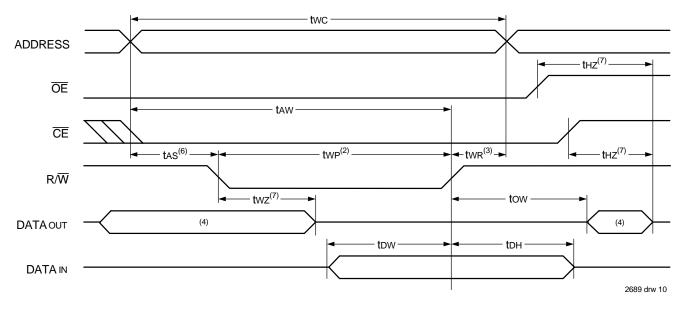
Output Active from End-of-Write⁽¹⁾

4. If OE is LOW during a RIW controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off data to be placed on the bus for the required tbw. If OE is HIGH during a R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

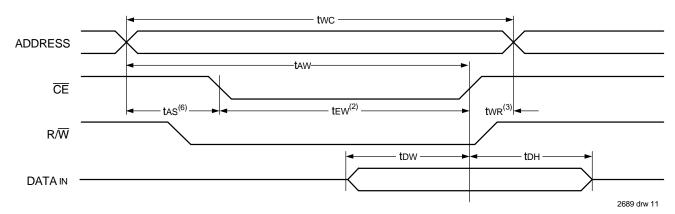
5. 'X' in part numbers indicates power rating (SA or LA).

Military, Industrial and Commercial Temperature Ranges

Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)^(1,5,8)



Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)^(1,5)



- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of $\overline{CE} = VIL$ and $R/\overline{W} = VIL$.
- 3. two is measured from the earlier of \overline{CE} or R/W going HIGH to the end of the write cycle.
- During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the HIGH impedance state.
- 6. Timing depends on which enable signal (\overline{CE} or $\overline{R/W}$) is asserted last.
- 7. This parameter is determined by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during a R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁷⁾

| | | 7130X20 ⁽¹⁾ 7140X20 ⁽¹⁾ Com'l Only | | | 7130X25 7140X25 Com'l, Ind & Military | | 7130X35 7140X35 Com'l & Military | |
|--------------|--|--|------|------|--|-------------|---|-------------|
| Symbol | Parameter | Min. | Мах. | Min. | Мах. | Min. | Мах. | Unit |
| BUSY TIMING | (For MASTER IDT 7130) | | | | | | | |
| tbaa | BUSY Access Time from Address | — | 20 | _ | 20 | | 20 | ns |
| tBDA | BUSY Disable Time from Address | | 20 | _ | 20 | | 20 | ns |
| tBAC | BUSY Access Time from Chip Enable | | 20 | _ | 20 | | 20 | ns |
| tBDC | BUSY Disable Time from Chip Enable | — | 20 | _ | 20 | _ | 20 | ns |
| twн | Write Hold After BUSY ⁽⁶⁾ | 12 | | 15 | — | 20 | _ | ns |
| twdd | Write Pulse to Data Delay ⁽²⁾ | — | 40 | - | 50 | | 60 | ns |
| todd | Write Data Valid to Read Data Delay ⁽²⁾ | | 30 | | 35 | | 35 | ns |
| taps | Arbitration Priority Set-up Time ⁽³⁾ | 5 | | 5 | | 5 | | ns |
| tBDD | BUSY Disable to Valid Data ⁽⁴⁾ | | 25 | | 35 | | 35 | ns |
| BUSY INPUT | TIMING (For SLAVE IDT 7140) | | | | | | | |
| twв | Write to BUSY Input ⁽⁵⁾ | 0 | | 0 | | 0 | | ns |
| twн | Write Hold After BUSY ⁽⁶⁾ | 12 | | 15 | | 20 | | ns |
| twdd | Write Pulse to Data Delay ⁽²⁾ | — | 40 | | 50 | | 60 | ns |
| todd | Write Data Valid to Read Data Delay ⁽²⁾ | | 30 | | 35 | | 35 | ns |
| | | | | | | | | 2689 tbl 11 |
| | | | | | | 7140 Com | 0X100 0X100 'I, Ind ilitary | |
| Symbol | Parameter | | | Min. | Max. | Min. | Max. | Unit |
| BUSY TIMING | (For MASTER IDT 7130) | | | | - | - | | |
| tbaa | BUSY Access Time from Address] | | | | 30 | | 50 | ns |
| tBDA | BUSY Disable Time from Address | | | | 30 | | 50 | ns |
| t BAC | BUSY Access Time from Chip Enable | | | 30 | _ | 50 | ns | |
| tBDC | BUSY Disable Time from Chip Enable | | 30 | | 50 | ns | | |
| twн | Write Hold After BUSY ⁽⁶⁾ | 20 | | 20 | | ns | | |
| twdd | Write Pulse to Data Delay ⁽²⁾ | | 80 | | 120 | ns | | |
| todd | Write Data Valid to Read Data Delay ⁽²⁾ | | 55 | | 100 | ns | | |
| taps | Arbitration Priority Set-up Time ⁽³⁾ | 5 | | 5 | | ns | | |
| tBDD | BUSY Disable to Valid Data ⁽⁴⁾ | | | 55 | | 65 | ns | |
| BUSY INPUT | TIMING (For SLAVE IDT 7140) | | | | | • | | - |
| | | | | | | | | |

twв Write to BUSY Input(5) 0 0 ns Write Hold After BUSY⁽⁶⁾ twн 20 20 ns Write Pulse to Data Delay⁽²⁾ 80 _____ 120 twdd _ ns Write Data Valid to Read Data $\mbox{Delay}^{(\!2\!)}$ todd 55 ____ 100 ns

NOTES:

1. PLCC, TQFP and STQFP packages only.

2. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port -to-Port Read and BUSY."

3. To ensure that the earlier of the two ports wins.

4. tbbb is a calculated parameter and is the greater of 0, twbb - twp (actual) or tbbb - tbw (actual).

5. To ensure that a write cycle is inhibited on port 'B' during contention on port 'A'.

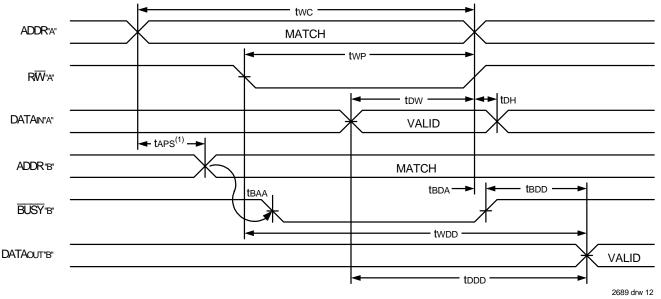
6. To ensure that a write cycle is completed on port 'B' after contention on port 'A'.

7. 'X' in part numbers indicates power rating (S or L).

2689 tbl 11b

Military, Industrial and Commercial Temperature Ranges

Timing Waveform of Write with Port-to-Port Read and **BUSY**^(2,3,4)

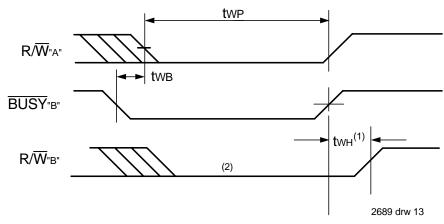


NOTES:

- 1. To ensure that the earlier of the two ports wins. tBDD is ignored for slave (IDT7140).
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port.

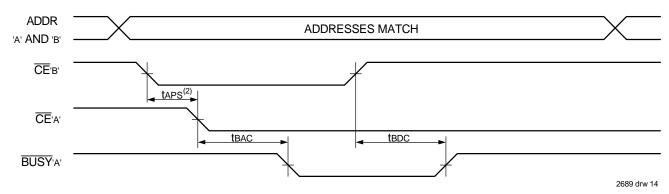
4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of Write with **BUSY**⁽³⁾

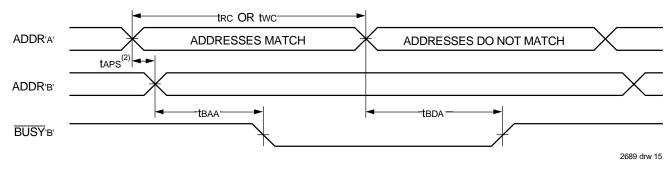


- 1. twH must be met for both BUSY Input (IDT7140, slave) or Output (IDT7130 master).
- 2. BUSY is asserted on port "B" blocking R/W B", until BUSY B" goes HIGH.
- 3. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is oppsite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



Timing Waveform by **BUSY** Arbitration Controlled by Address Match Timing⁽¹⁾



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (7130 only).

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽²⁾

| | | 7140 | X20 ⁽¹⁾ X20 ⁽¹⁾ I Only | 714 Com | 0X25 0X25 'I, Ind litary | 714 Co | 0X35 0X35 om'l ilitary | |
|-----------|----------------------|------|--|------------|-----------------------------------|-----------|---------------------------------|------|
| Symbol | Parameter | Min. | Мах. | Min. | Мах. | Min. | Мах. | Unit |
| INTERRUPT | TIMING | | | | | | | |
| tas | Address Set-up Time | 0 | | 0 | _ | 0 | | ns |
| twr | Write Recovery Time | 0 | | 0 | _ | 0 | _ | ns |
| tins | Interrupt Set Time | _ | 20 | _ | 25 | | 25 | ns |
| tinr | Interrupt Reset Time | | 20 | | 25 | | 25 | ns |
| unix | | | 20 | | 25 | | | |

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NOTES:

1. PLCC, TQFP and STQFP package only.

2. 'X' in part numbers indicates power rating (SA or LA).

2689 tbl 12a

Military, Industrial and Commercial Temperature Ranges

2689 tbl 12b

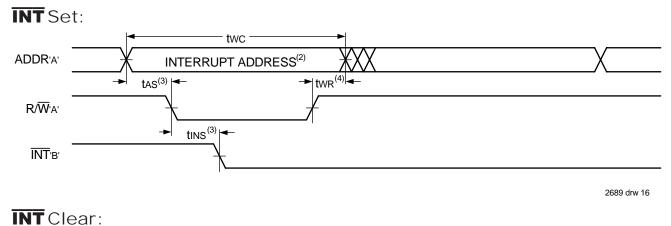
AC Electrical characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

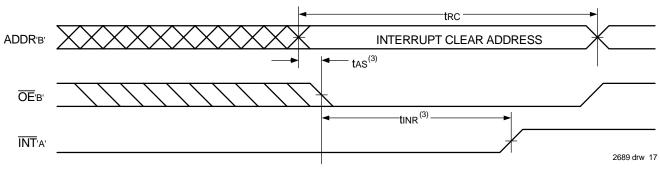
| | | 7130X55 7130X10 7140X55 7140X10 Com'l, Ind Com'l, In & Military & Militar | | | X100 'I, Ind | |
|-------------|----------------------|--|------|------|-----------------|------|
| Symbol | Parameter | Min. | Max. | Min. | Max. | Unit |
| INTERRUPT T | IMING | | | - | | |
| tas | Address Set-up Time | 0 | | 0 | | ns |
| twr | Write Recovery Time | 0 | | 0 | | ns |
| tins | Interrupt Set Time | | 45 | | 60 | ns |
| tinr | Interrupt Reset Time | | 45 | | 60 | ns |

NOTES:

1. 'X' in part numbers indicates power rating (SA or LA).

Timing Waveform of Interrupt Mode⁽¹⁾





NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. See Interrupt Truth Table II.

- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal (CE or R/W) is de-asserted first.

Truth Tables

Truth Table I — Non-Contention Read/Write Control⁽⁴⁾

| Inputs ⁽¹⁾ | | | | |
|-----------------------|---|----|---------|--|
| R/W | Ē | ŌĒ | D0-7 | Function |
| Х | Н | Х | Z | Port Disabled and in Power-Down Mode, IsB2 or IsB4 |
| Х | Н | Х | Z | $\overline{CE}R = \overline{CE}L = VH$, Power-Down Mode, ISB1 or ISB3 |
| L | L | Х | DATAIN | Data on Port Written into Memory ⁽²⁾ |
| Н | L | L | DATAOUT | Data in Memory Output on Port ⁽³⁾ |
| Н | L | Н | Z | High Impedance Outputs |

NOTES:

1. A0L – A10L \neq A0R – A10R.

2. If $\overline{\text{BUSY}}$ = L, data is not written.

3. If $\overline{\text{BUSY}} = L$, data may not be valid, see twod and todd timing.

4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Truth Table II — Interrupt Flag^(1,4)

| | Left Port | | | | | Right Port | | | | |
|------|-----------|-----|---------|------------------|------|------------|-----|---------|------------------|-----------------------|
| R/₩L | ĊĒ∟ | OEL | A9L-A0L | ĨNT∟ | R/WR | ĊĒr | ŌĒR | A9R-A0R | Ī NT R | Function |
| L | L | Х | 3FF | Х | Х | Х | Х | Х | L ⁽²⁾ | Set Right INTR Flag |
| Х | Х | Х | Х | Х | Х | L | L | 3FF | H ⁽³⁾ | Reset Right INTR Flag |
| Х | Х | Х | Х | L ⁽³⁾ | L | L | Х | 3FE | Х | Set Left INTL Flag |
| Х | L | L | 3FE | H ⁽²⁾ | Х | Х | Х | Х | Х | Reset Left INT∟ Flag |

NOTES:

1. Assumes $\overline{BUSY}L = \overline{BUSY}R = VIH$

2. If $\overline{\text{BUSY}}L = VIL$, then No Change.

3. If BUSYR = VIL, then No Change.

4. 'H' = HIGH,' L' = LOW,' X' = DON'T CARE

Truth Table III — Address **BUSY** Arbitration

| | In | puts | Out | puts | |
|-----|-------------|--------------------|----------------------|------------------------------|------------------------------|
| ĒĒ∟ | CE R | Aol-A9l Aor-A9r | BUSYL ⁽¹⁾ | BUSY R ⁽¹⁾ | Function |
| Х | Х | NO MATCH | Н | Н | Normal |
| Н | Х | MATCH | Н | Н | Normal |
| Х | Н | MATCH | Н | Н | Normal |
| L | L | MATCH | (2) | (2) | Write Inhibit ⁽³⁾ |

NOTES:

- Pins BUSYL and BUSYR are both outputs for IDT7130 (master). Both are inputs for IDT7140 (slave). BUSYX outputs on the IDT7130 are open drain, not push-pull outputs. On slaves the BUSYX input internally inhibits writes.
- 2. 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either \overline{BUSY}_{L} or $\overline{BUSY}_{R} = LOW$ will result. \overline{BUSY}_{L} and \overline{BUSY}_{R} outputs can not be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

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2689 tbl 15

2689 tbl 14

2689 tbl 13

Functional Description

The IDT7130/IDT7140 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7130/IDT7140 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls onchip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = VIH$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location 3FE (HEX), where a write is defined as the $\overline{CER} = R/\overline{WR} = VIL$ per Truth Table II. The left port clears the interrupt by accessing address location 3FE when $\overline{CEL} = \overline{OEL} = VIL, R/\overline{W}$ is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 3FF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must access the memory location 3FF. The message (8 bits) at 3FE or 3FF is user-defined, since it is an addressable SRAMIocation. If the interrupt function is not used, address locations 3FE and 3FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

BusyLogic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of $\overline{\text{BUSY}}$ logic is not required or desirable for all applications. In some cases it may be useful to logically OR the $\overline{\text{BUSY}}$ outputs together and use any $\overline{\text{BUSY}}$ indication as an interrupt source to flag the event of an illegal or illogical operation. In slave mode the $\overline{\text{BUSY}}$ pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the $\overline{\text{BUSY}}$ pins HIGH. If desired, unintended write operations can be prevented to a port by tying the $\overline{\text{BUSY}}$ pin for that port LOW.

The BUSY outputs on the IDT7130 RAM (Master) are open drain type outputs and require open drain resistors to operate. If these

RAMs are being expanded in depth, then the BUSY indication for the resulting array does not require the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an RAM array in width while using busy logic, one master part is used to decide which side of the RAM array will receive a busy indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the busy signal as a write inhibit signal. Thus on the IDT7130/IDT7140 RAMs the BUSY pin is an output if the part is Master (IDT7130), and the BUSY pin is an input if the part is a Slave (IDT7140) as shown in Figure 3.

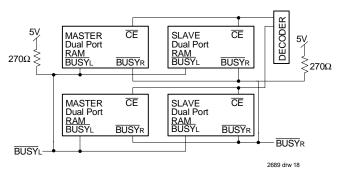
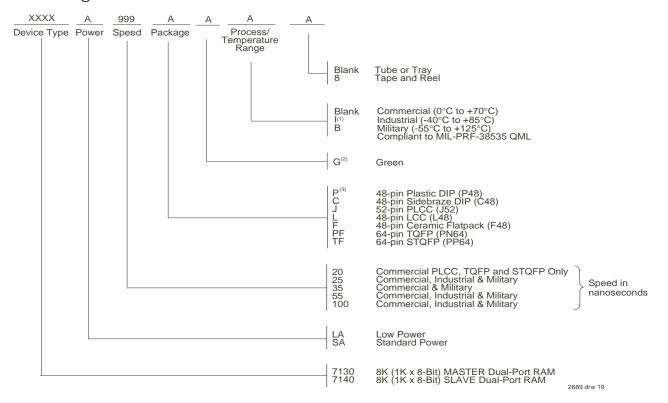


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7130 (Master) and IDT7140 (Slave)RAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating busy on one side of the array and another master indicating busy on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with either the R/W signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Ordering Information



NOTES:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.
- LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice PDN# SP-17-02

3. For "P", plastic DIP, when ordering green package the suffix is "PDG".

Datasheet Document History

| 03/15/99: | | Initiated datasheet document history Converted to new format |
|-----------|-------------------|--|
| | | Cosmetic and typographical corrections |
| | Pages 2 and 3 | Added additional notes to pin configurations |
| 06/08/99: | | Changed drawing format |
| 08/02/99: | Page 2 | Corrected package number in note 3 |
| 09/29/99: | Page 2 | Fixed pin 1 in DIP pin configuration |
| 11/10/99: | Page 1 & 18 | Replaced IDT logo |
| 06/23/00: | Page 4 | Increased storage temperature parameters |
| | 0 | Clarified TA parameter |
| | Page 5 | DC Electrical parameters-changed wording from "open" to "disabled" |
| | Page 10 | Changed ±500mV to 0mV in notes |
| 01/08/02: | Page 1 | Added Ceramic Flatpack to 48-pin package offerings |
| | Page 2 & 3 | Added date revision to pin configurations |
| | Page 4, 5, 8, 10, | Removed industrial temp option footnote from all tables |
| | 12,14 & 15 | |

i

Datasheet Document History (cont'd)

| 01/08/02: | Page 5, 8, 10, 12, & 14 | Added industrial temp for 25ns to DC & AC Electrical Characteristics |
|-----------|-------------------------|--|
| | Page 5, 8, 10, 12, & 14 | Removed industrial temp for 35ns to DC & AC Electrical Characteristics |
| | Page 18 | Added industrial temp for 25ns and removed industrial temp for 35ns in ordering information |
| | - | Updated industrial temp option footnote |
| | Page 1 & 19 | Replaced IDT ™ logo with IDT [®] logo |
| 01/11/06: | Page 1 | Added green availability to features |
| | Page 18 | Added green indicator to ordering information |
| | Page 1 & 19 | Replaced old IDT TM with new IDT TM logo |
| 04/14/06: | Page 18 | Added "PDG" footnote to the ordering information |
| 10/21/08: | Page 18 | Removed "IDT" from orderable part number |
| 01/21/13: | Page 2 | Added L48-1 package and F48-1 package pin configurations |
| | - | with corresponding foot notes |
| | Page 13, 18, 19 & 20 | Typo/corrections |
| | Page 20 | Added T & Reel indicator to ordering information |
| 05/20/16: | Page 2 | Split the F48 and L48 pin configuration, creating two separate pin configurations: |
| | - | F48 pin ceramic flatpack rotated 90 degrees counterclockwise, removed footnote 5 reference |
| | | and L48 LCC rotated 90 degrees clockwise to reflect pin 1 orientation and added dot at pin 1, |
| | | removed footnote 5 reference |
| | Page 3 | P48 plastic DIP and C48 sidebrazed DIP, removed half moon and to reflect pin 1 orientation |
| | - | added dot at pin 1 |
| | Page 4 | J52 PLCC rotated 90 degrees clockwise to reflect pin 1 orientation added dot at pin 1, removed |
| | | footnote 5 reference |
| | Page 5 | PN64 TQFP and PP64 STQFP, chamfer removed, rotated 90 degrees counterclockwise to |
| | | reflect pin 1 orientation and added dot at pin 1, removed footnote 5 reference |
| | Page 20 | All incidences of -1, -2 have been removed from the datasheet |
| 02/13/18: | | Product Discontinuation Notice - PDN# SP-17-02 |
| | | Last time buy expires June 15, 2018 |
| | | |

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